

HiPerFET™ Power MOSFETs

IXFK 150N15 IXFX 150N15

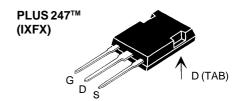
 $V_{DSS} = 150 V$ $I_{D25} = 150 A$ $R_{DS(on)} = 12.5 m\Omega$

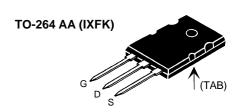
 $t_{rr} \leq$ 250 ns

Single MOSFET Die

Preliminary data sheet

Symbol	Test Conditions	Maximu	Maximum Ratings		
V _{DSS}	T _J = 25°C to 150°C	150			
V_{DGR}	$T_J^{\circ} = 25^{\circ}C$ to $150^{\circ}C$; $R_{GS} = 1 M\Omega$	150	V		
V _{GS}	Continuous	±20	V		
V _{GSM}	Transient	±30	V		
I _{D25}	T _C = 25°C (MOSFET chip capability)	150	Α		
D(RMS)	External lead (current limit)	76	A		
I _{DM}	$T_{\rm C} = 25^{\circ}$ C, Note 1	600	Α		
I _{AR}	$T_{c} = 25^{\circ}C$	150	A		
E _{AR}	T _C = 25°C	60	mJ		
E _{AS}	$T_{c}^{-} = 25^{\circ}C$	3	J		
dv/dt	$\begin{array}{ll} I_{S} & \leq I_{DM}, di/dt \leq 100 A/\mu s, V_{DD} \leq V_{DSS} \\ T_{J} & \leq 150^{\circ} C, R_{G} = 2 \Omega \end{array}$	5	V/ns		
P _D	T _C = 25°C	560	W		
T _J		-55 +150	°C		
T_{JM}		150	°C		
T _{stg}		-55 + 150	°C		
T _L	1.6 mm (0.063 in.) from case for 10 s	300	°C		
M _d	Mounting torque TO-264	0.9/6	Nm/lb.in.		
Weight	PLUS 247		6 g		
	TO-264		10 g		





G = Gate	D = Drain
S = Source	TAB = Drain

Features

- International standard packages
- Low R_{DS (on)} HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
- easy to drive and to protect
- Fast intrinsic rectifier

Symbol	Test Conditions	Characteristic Values		
		$(T_J = 25^{\circ}C, \text{ unless otherwise specified})$		
		min.	typ.	max.

V _{DSS}	$V_{GS} = 0 \text{ V}, I_D = 3\text{mA}$	150	V
V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 8mA$	2.0	4.0 V
I _{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$		±100 nA
I _{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0 V$	$T_J = 25^{\circ}C$ $T_J = 125^{\circ}C$	100 μA 2 mA
R _{DS(on)}	$V_{GS} = 10 \text{ V}, I_{D} = 0.5 \bullet I_{D25}$ Note 1		12.5 mΩ

Applications

- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- · AC motor control
- Temperature and lighting controls

Advantages

- PLUS 247[™] package for clip or spring mounting
- Space savings
- High power density

IXYS reserves the right to change limits, test conditions, and dimensions.

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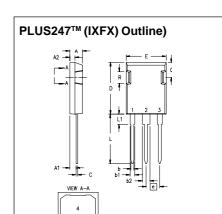
Symbol	Test Conditions	(T _J = 25°0	Cha C, unless o min.	aracter otherwis typ.		
g _{fs}	$V_{DS} = 10 \text{ V}; I_{D} = 60 \text{A}$	Note 2	50	75		S
C _{iss})			9100		pF
C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}$	V, f = 1 MHz		2600		pF
\mathbf{C}_{rss}	J			1200		pF
t _{d(on)})			50		ns
t _r	$V_{GS} = 10 \text{ V}, V_{DS} = 0.8$	$5 \bullet V_{DSS}, I_{D} = 0.5$	• I _{D25}	60		ns
t _{d(off)}	$R_{\rm G} = 1 \Omega$ (External),			110		ns
$\mathbf{t}_{_{\mathbf{f}}}$)			45		ns
Q _{g(on)})			360		nC
Q_{gs}	$V_{GS} = 10 \text{ V}, V_{DS} = 0.9$	$5 \cdot V_{DSS}, I_D = 0.5$	• I _{D25}	65		nC
\mathbf{Q}_{gd}	J			190		nC
R _{thJC}					0.22	K/W
R _{thCK}				0.15		K/W

Source-Drain Diode

Characteristic Values $(T_1 = 25^{\circ}C, unless otherwise specified)$

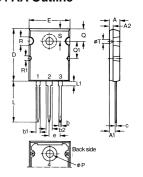
Symbol	Test Conditions	min.	typ.	max.	,
I _s	V _{GS} = 0 V			150	Α
I _{SM}	Repetitive; pulse width limited by T _{JM}			600	Α
V _{SD}	$I_F = 100A, V_{GS} = 0 V, Note 1$			1.5	V
t _{rr}				250	ns
\mathbf{Q}_{RM}	$I_F = 50A, -di/dt = 100 A/\mu s, V_R = 50 V$		1.1		μС
I _{RM}	J		13		Α

Note: 1. Pulse width limited by T_{JM} 2. Pulse test, $t \le 300~\mu s$, duty cycle $d \le 2~\%$



Dim.	Millimeter		Inches
	Min.	Max.	Min. Max.
Α	4.83	5.21	.190 .205
A,	2.29	2.54	.090 .100
A ₂	1.91	2.16	.075 .085
b	1.14	1.40	.045 .055
b ₁	1.91	2.13	.075 .084
b ₂	2.92	3.12	.115 .123
С	0.61	0.80	.024 .031
D	20.80	21.34	.819 .840
Е	15.75	16.13	.620 .635
е	5.45	BSC	.215 BSC
L	19.81	20.32	.780 .800
L1	3.81	4.32	.150 .170
Q	5.59	6.20	.220 .244
R	4.32	4.83	.170 .190

TO-264 AA Outline



Dim.	Millimeter			hes	
	Min.	Max.	Min.	Max.	
Α	4.82	5.13	.190	.202	
Α1	2.54	2.89	.100	.114	
A2	2.00	2.10	.079	.083	
b	1.12	1.42	.044	.056	
b1	2.39	2.69	.094	.106	
b2	2.90	3.09	.114	.122	
С	0.53	0.83	.021	.033	
D	25.91	26.16	1.020	1.030	
Е	19.81	19.96	.780	.786	
е	5.46	BSC	.215 BSC		
J	0.00	0.25	.000	.010	
K	0.00	0.25	.000	.010	
L	20.32	20.83	.800	.820	
L1	2.29	2.59	.090	.102	
Р	3.17	3.66	.125	.144	
Q	6.07	6.27	.239	.247	
Q1	8.38	8.69	.330	.342	
R	3.81	4.32	.150	.170	
R1	1.78	2.29	.070	.090	
S	6.04	6.30	.238	.248	
T	1.57	1.83	.062	.072	

